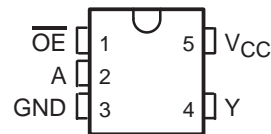


SN74AHC1G125 SINGLE BUS BUFFER GATE WITH 3-STATE OUTPUT

SCLS377E – AUGUST 1997 – REVISED JANUARY 2000

- **EPIC™ (Enhanced-Performance Implanted CMOS) Process**
- **Operating Range 2-V to 5.5-V V_{CC}**
- **Package Options Include Plastic Small-Outline Transistor (DBV, DCK) Packages**

DBV OR DCK PACKAGE
(TOP VIEW)



description

The SN74AHC1G125 is a single bus buffer gate/line driver with 3-state output. The output is disabled when the output-enable (\overline{OE}) input is high. When \overline{OE} is low, true data is passed from the A input to the Y output.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74AHC1G125 is characterized for operation from -40°C to 85°C .

FUNCTION TABLE

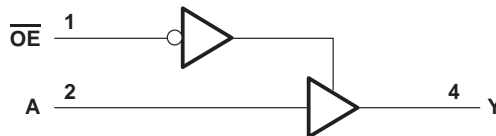
INPUTS		OUTPUT
\overline{OE}	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



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**TEXAS
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SN74AHC1G125

SINGLE BUS BUFFER GATE

WITH 3-STATE OUTPUT

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	-0.5 V to 7 V
Input voltage range, V_I (see Note 1)	-0.5 V to 7 V
Output voltage range, V_O (see Note 1)	-0.5 V to $V_{CC} + 0.5$ V
Input clamp current, I_{IK} ($V_I < 0$)	-20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$)	±20 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})	±25 mA
Continuous current through V_{CC} or GND	±50 mA
Package thermal impedance, θ_{JA} (see Note 2): DBV package	347°C/W
DCK package	389°C/W
Storage temperature range, T_{stg}	-65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 3)

		MIN	MAX	UNIT
V_{CC}	Supply voltage	2	5.5	V
V_{IH}	High-level input voltage	$V_{CC} = 2$ V	1.5	V
		$V_{CC} = 3$ V	2.1	
		$V_{CC} = 5.5$ V	3.85	
V_{IL}	Low-level input voltage	$V_{CC} = 2$ V	0.5	V
		$V_{CC} = 3$ V	0.9	
		$V_{CC} = 5.5$ V	1.65	
V_I	Input voltage	0	5.5	V
V_O	Output voltage	0	V_{CC}	V
I_{OH}	High-level output current	$V_{CC} = 2$ V	-50	µA
		$V_{CC} = 3.3$ V ± 0.3 V	-4	mA
		$V_{CC} = 5$ V ± 0.5 V	-8	
I_{OL}	Low-level output current	$V_{CC} = 2$ V	50	µA
		$V_{CC} = 3.3$ V ± 0.3 V	4	mA
		$V_{CC} = 5$ V ± 0.5 V	8	
$\Delta t/\Delta v$	Input transition rise or fall rate	$V_{CC} = 3.3$ V ± 0.3 V	100	ns/V
		$V_{CC} = 5$ V ± 0.5 V	20	
T_A	Operating free-air temperature	-40	85	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	T _A = 25°C			MIN	MAX	UNIT
			MIN	TYP	MAX			
V _{OH}	I _{OH} = -50 μA	2 V	1.9	2		1.9	V	
		3 V	2.9	3		2.9		
		4.5 V	4.4	4.5		4.4		
	I _{OH} = -4 mA	3 V	2.58		2.48			
	I _{OH} = -8 mA	4.5 V	3.94		3.8			
V _{OL}	I _{OL} = 50 μA	2 V			0.1	0.1	V	
		3 V			0.1	0.1		
		4.5 V			0.1	0.1		
	I _{OL} = 4 mA	3 V			0.36	0.44		
	I _{OL} = 8 mA	4.5 V			0.36	0.44		
I _I	V _I = V _{CC} or GND	0 V to 5.5 V			±0.1	±1	μA	
I _{OZ}	V _I = V _{CC} or GND	5.5 V			±0.25	±2.5	μA	
I _{CC}	V _I = V _{CC} or GND, I _O = 0	5.5 V			1	10	μA	
C _i	V _I = V _{CC} or GND	5 V		4	10	10	pF	
C _o	V _O = V _{CC} or GND	5 V		10			pF	

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T _A = 25°C			MIN	MAX	UNIT
				MIN	TYP	MAX			
t _{PLH}	A	Y	C _L = 15 pF		5.6	8	1	9.5	ns
t _{PHL}					5.6	8	1	9.5	
t _{PZH}	\overline{OE}	Y	C _L = 15 pF		5.4	8	1	9.5	ns
t _{PZL}					5.4	8	1	9.5	
t _{PHZ}	\overline{OE}	Y	C _L = 15 pF		7	9.7	1	11.5	ns
t _{PLZ}					7	9.7	1	11.5	
t _{PLH}	A	Y	C _L = 50 pF		8.1	11.5	1	13	ns
t _{PHL}					8.1	11.5	1	13	
t _{PZH}	\overline{OE}	Y	C _L = 50 pF		7.9	11.5	1	13	ns
t _{PZL}					7.9	11.5	1	13	
t _{PHZ}	\overline{OE}	Y	C _L = 50 pF		9.5	13.2	1	15	ns
t _{PLZ}					9.5	13.2	1	15	



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switching characteristics over recommended operating free-air temperature range,
 $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$ (unless otherwise noted) (see Figure 1)

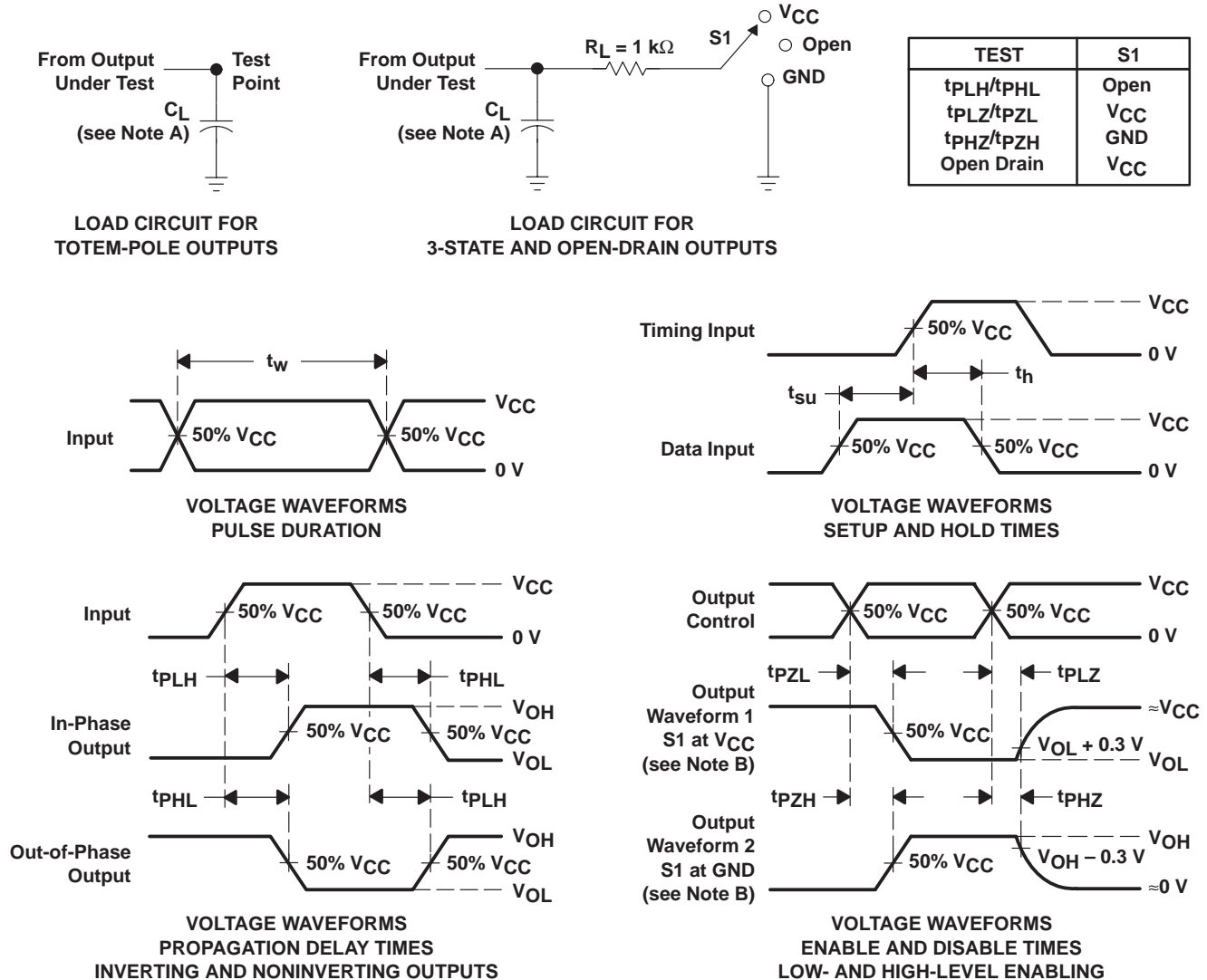
PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	$T_A = 25^\circ\text{C}$			MIN	MAX	UNIT
				MIN	TYP	MAX			
t_{PLH}	A	Y	$C_L = 15\text{ pF}$	3.8	5.5	1	6.5	ns	
t_{PHL}				3.8	5.5	1	6.5		
t_{PZH}	\overline{OE}	Y	$C_L = 15\text{ pF}$	3.6	5.1	1	6	ns	
t_{PZL}				3.6	5.1	1	6		
t_{PHZ}	\overline{OE}	Y	$C_L = 15\text{ pF}$	4.6	6.8	1	8	ns	
t_{PLZ}				4.6	6.8	1	8		
t_{PLH}	A	Y	$C_L = 50\text{ pF}$	5.3	7.5	1	8.5	ns	
t_{PHL}				5.3	7.5	1	8.5		
t_{PZH}	\overline{OE}	Y	$C_L = 50\text{ pF}$	5.1	7.1	1	8	ns	
t_{PZL}				5.1	7.1	1	8		
t_{PHZ}	\overline{OE}	Y	$C_L = 50\text{ pF}$	6.1	8.8	1	10	ns	
t_{PLZ}				6.1	8.8	1	10		

operating characteristics, $V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	TYP	UNIT
C_{pd} Power dissipation capacitance	No load, $f = 1\text{ MHz}$	14	pF



PARAMETER MEASUREMENT INFORMATION



- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 3 ns, t_f ≤ 3 ns.
 D. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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